

SI2324DS

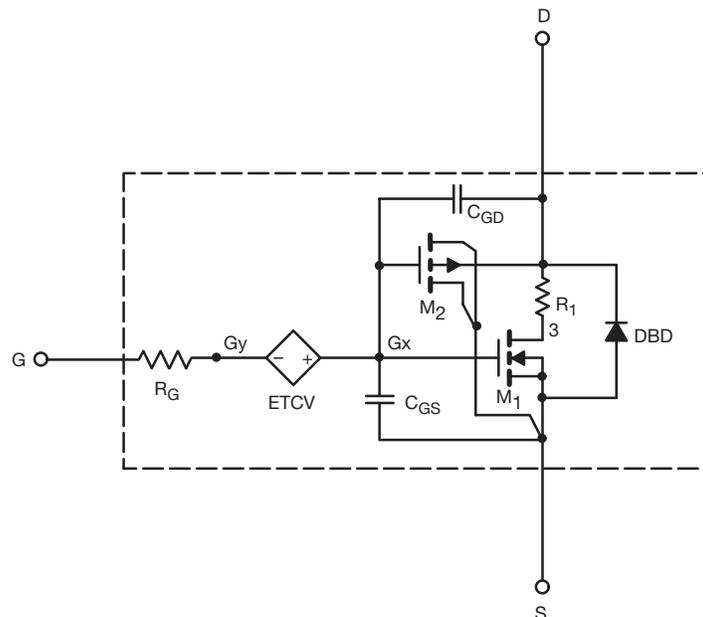
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.8	-	V
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 1.5\ \text{A}$	0.199	0.195	Ω
		$V_{GS} = 6\ \text{V}, I_D = 1\ \text{A}$	0.222	0.222	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 20\ \text{V}, I_D = 4.6\ \text{A}$	3	2	S
Body Diode Voltage	V_{SD}	$I_S = 1.3\ \text{A}$	0.79	0.80	V
Dynamic^b					
Input Capacitance	C_{iss}	$V_{DS} = 20\ \text{V}, V_{GS} = 0\ \text{V}, f = 1\ \text{MHz}$	190	190	pF
Output Capacitance	C_{oss}		22	22	
Reverse Transfer Capacitance	C_{rss}		15	13	
Total Gate Charge	Q_g	$V_{DS} = 50\ \text{V}, V_{GS} = 10\ \text{V}, I_D = 1.6\ \text{A}$	4.1	5.2	nC
		$V_{DS} = 50\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 1.6\ \text{A}$	2.5	2.9	
Gate-Source Charge	Q_{gs}		0.75	0.75	
Gate-Drain Charge	Q_{gd}		1.4	1.4	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\ \%$.
b. Guaranteed by design, not subject to production testing.